

**FORM PTO-1449 U.S. DEPARTMENT OF
COMMERCE
(Rev. 2-32) PATENT AND TRADEMARK OFFICE**

ATTY. DOCKET NO.
30-4687 (4790)

SERIAL NO.:

09/328,646



**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

APPLICANT:
SHI-QING WANG, ET AL

(Use several sheets if necessary)

FILING DATE:

06/09/99

GROUP:

2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Vu	AA	5,693,566	12/02/1997	Cheung	437	195	—
Vu	AB	5,864,172	01/26/1999	Kapoor, et al.	257	634	—
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	YES	NO
Vu	AL	0 680 085 A1	04/28/1995	02/11/95 Europe	—	—	✓		
Vu	AM	0 692 824 A2	07/14/1995	01/17/96 Europe	—	—	✓		
Vu	AN	0 805 491 A2	04/29/1997	05/11/97 Europe	—	—	✓		
Vu	AO	0 849 796 A2	12/16/1997	06/24/98 Europe	—	—	✓		
	AP								
	AQ								

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

Vu	AR	XP 000300654, Multilevel Interconnection Structure, IBM Technical Disclosure Bulletin, Vol. 34, No. 9, February 1992, p. 220.
Vu	AS	XP 000583029, Low Dielectric Constant Materials for Interlayer Dielectric Applications, Shyam P. Murarka, Solid State Technology, March 1996, No. 3, Tulsa, OK, US, pp 3 - 7.
Vu	AT	XP-000952344, Processing and Characterization of Silica Xerogel Films for Low-K Dielectric Applications, Anarag Jain, et al., Mat. Res. Soc. Symp. Proc. Vol. 565, 1999, Materials Research Society, pp 8-19.

EXAMINER

HUNG K VU

DATE CONSIDERED

07/10/01

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

#11

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. 30-4687 (4790)	SERIAL NO.: 09/328,646 RECEIVED
INFORMATION DISCLOSURE STATEMENT BY APPLICANT			APPLICANT: SHI-QING WANG, ET AL	MAY 30 2001
(Use several sheets if necessary)			FILING DATE: 06/09/01	GROUP: TECHNOLOGY CENTER 2800 2811

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Vu	AA	5,858,869	01/12/1999	Chen, et al.	438	597	-
Vu	AB	6,080,526	06/27/2000	Yang, et al.	430	296	-
Vu	AC	6,097,095	08/01/2000	Chung	257	774	-
Vu	AD	6,124,198	09/26/2000	Moslehi	438	622	-
Vu	AE	6,143,641	11/07/2000	Kitch	438	618	-
Vu	AF	6,165,893	12/26/2000	Chung	438	623	-
Vu	AG	6,207,555	03/27/2001	Ross	438	633	-
Vu	AH	6,211,063	04/03/2001	Liu, et al.	438	624	-
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
	AL						
	AM						
	AN						
	AO						
	AP						
	AQ						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

Vu	AR	"HIGH STUD-TO-LINE CONTACT AREA IN DAMASCENE METAL PROCESSING", IBM TECHNICAL DISCLOSURE BULLETIN, VOL. 33, NO. 1A, JUNE 1990, PA. 160-161.
	AS	
	AT	

EXAMINER HUNG K. VU DATE CONSIDERED 07/10/01

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE (Rev. 2-32) PATENT AND TRADEMARK OFFICE				ATTY. DOCKET NO: 30-4687 (4790)	SERIAL NO.: 09/328,646		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				APPLICANT: SHI-QING WANG, ET AL			
(Use several sheets if necessary)				FILING DATE: 06/09/99	GROUP: 2811		
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
V	AA	5,801,095	9/01/98	YEW, ET AL	438	624	-
AB							
AC							
AD							
AE							
AF							
AG							
AH							
AI							
AJ							
AK							
FOREIGN PATENT DOCUMENTS							
							TRANSLATION
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	YES NO
AL							
AM							
AN							
AO							
AP							
AQ							
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
V	AR	"HIGH STUD-TO-LINE CONTACT AREA IN DAMASCENE METAL PROCESSING"; IBM TECHNICAL DISCLOSURE BULLETIN, VOL. 33, NO. IA, JUNE 1990, PP. 160-161.					
	AS						
	AT						
EXAMINER		HUNG K. VU			DATE CONSIDERED		07/10/01
Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							